

# New Jersey Semi-Conductor Products, Inc.

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**JEDEC TYPE NO. 2N2015**

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## **I. General Description**

This device is an NPN silicon triode power transistor designed primarily for untuned amplifier applications.

## II. Mechanical Data

**A. Outline**  
**TQ-36**

## B. Terminal designations

<u>Terminal</u>	<u>Element</u>
1	Base
2	Emitter
Case	Collector

### III. Maximum Ratings

#### A. Temperature

1. Storage temperature range,  $T_{stg}$  . . . . . -65°C to +200°C
  2. Operating case temperature range,  $T_C$  . . . . . -65°C to +200°C

B. Voltage, at Case Temperature, T<sub>c</sub>, of 25°C



### C. Current

- |   |       |
|---|-------|
| 1. Continuous operating collector current . . . . . | 10 a  |
| 2. Continuous base current . . . . .                | 6 a   |
| 3. Continuous emitter current . . . . .             | -13 a |

D. Power

1. Continuous power dissipation at or below 25°C case . . . . . 150 w  
temperature (temperature measured at intersection of  
seating surface with mounting stud)

Linear derating factor 0.855 w/°C

IV. Electrical Characteristics, 25°C Case Temperature, unless otherwise specified

A. <u>Static</u>	<u>Min.</u>	<u>Max.</u>	
1. Collector cutoff current, $I_{CE0}$ . . . . . - 2 ma $V_{CE} = 30$ v, $V_{BE} = -1.5$ v, $T_C = 150^\circ\text{C}$			ma
2. Collector cutoff current, $I_{CE0}$ . . . . . - 2 ma $V_{CE} = 130$ v, $V_{BE} = -1.5$ v			ma
3. Emitter cutoff current, $I_{EB0}$ . . . . . - 0.05 ma $V_{EB} = 10$ v, $T_C = 25^\circ\text{C}$			ma
4. Collector-emitter open base sustain voltage, $V_{CEO}(\text{sus})$ . . . . . 50 - v $I_B = 0$ , $I_C = 200$ ma			v
5. Collector cutoff current, base open, $I_{CEO}$ - 0.2 ma $I_B = 0$ , $V_{CE} = 40$ v			ma
6. DC forward current transfer ratio, $h_{FE}$ . . . . 8 - $I_C = 9$ a, $V_{CE} = 4$ v			
7. DC forward current transfer ratio, $h_{FE}$ . . . . 15 50 $I_C = 5$ a, $V_{CE} = 4$ v			
8. Collector-emitter saturation voltage, $V_{CE}(\text{sat})$ - 1.25 v $I_C = 5$ a, $I_B = 0.5$ a			v
9. Base-emitter voltage, $V_{BE}$ . . . . . - 2.2 v $I_C = 5$ a, $V_{CE} = 4$ v			v

B. Dynamic

1. Common emitter small-signal short-circuit forward current transfer ratio cutoff frequency, $f_{hfe}$ . . . . . 12 - kc $V_{CE} = 4$ v, $I_C = 5$ a			
2. Common base output capacitance, $C_{ob}$ . . . . . - 400 pf $V_{CB} = 40$ v, $I_C = 50$ $\mu$ a, $f = 1$ Mc			pf
3. Common emitter small-signal short-circuit . . . 12 60 forward current transfer ratio, $h_{fe}$ $V_{CE} = 4$ v, $I_C = 1$ a, $f = 1$ kc			